



DSS3515M

15V PNP LOW V_{CE(sat)} TRANSISTOR

Features

- BV_{CEO} > -15V
- I_C = -500mA High Collector Current
- I_{CM} = -1A Peak Pulse Current
- P_D = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, V_{CE(sat)}
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DSS2515M
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

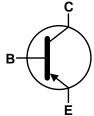
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

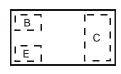
X1-DFN1006-3







Device Symbol



Top View Device Schematic

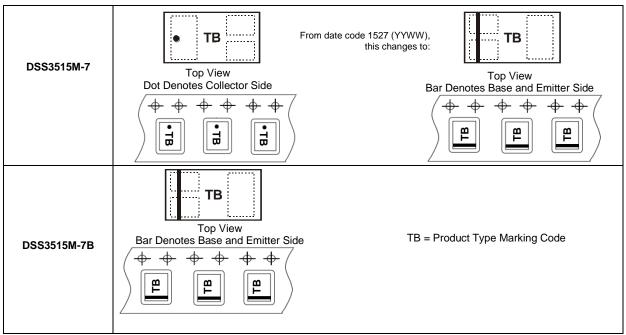
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS3515M-7	AEC-Q101	TB	7	8	3,000
DSS3515M-7B	AEC-Q101	TB	7	8	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-15	V
Collector-Emitter Voltage	V _{CEO}	-15	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current - Continuous	Ic	-500	mA
Peak Pulse Collector Current	Ісм	-1	Α
Peak Base Current	I _{BM}	-100	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	400		mW	
Fower Dissipation	(Note 6)	P _D	1000	ITIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	310		°C AN	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	120	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Rang	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

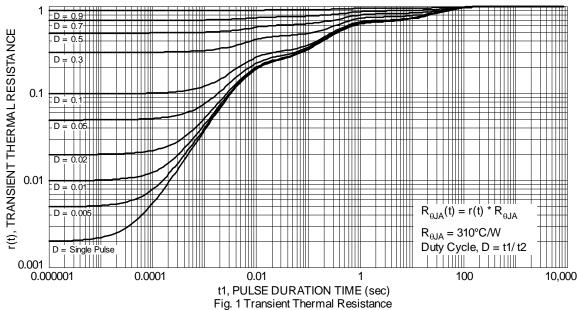
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

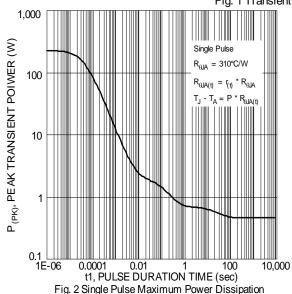
Notes:

- For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics







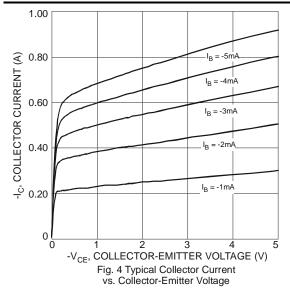
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

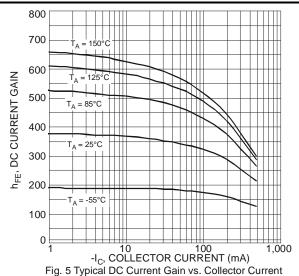
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-15			٧	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-15			V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_		V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	1			-100	nA	$V_{CB} = -15V, I_{E} = 0$
Collector Cuton Current	I _{CBO}	_		-50	μΑ	$V_{CB} = -15V$, $I_E = 0$, $T_A = +150$ °C
Emitter Cutoff Current	I _{EBO}	_		-100	nA	$V_{EB} = -5V, I_C = 0$
ON CHARACTERISTICS (Note 9)						
		200	_	_		$V_{CE} = -2V, I_{C} = -10mA$
DC Current Gain	h _{FE}	150	_	_	_	$V_{CE} = -2V, I_{C} = -100mA$
		90	—			$V_{CE} = -2V, I_{C} = -500mA$
		_	_	-25		$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	-150	mV	$I_C = -200 \text{mA}, I_B = -10 \text{mA}$
		_	_	-250		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	500	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-1.1	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	-0.9	V	V _{CE} = -2V, I _C = -100mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	_	10	pF	$V_{CB} = -10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f⊤	100	340	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz

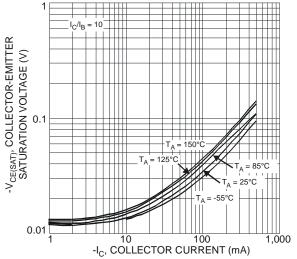
Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







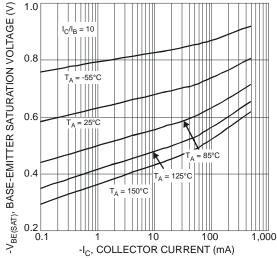
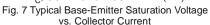
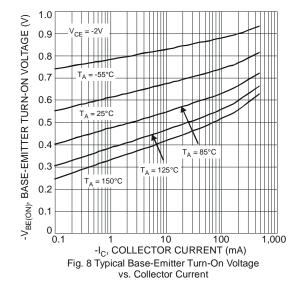


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current





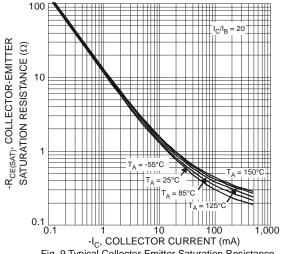
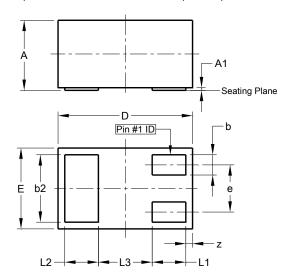


Fig. 9 Typical Collector-Emitter Saturation Resistance vs. Collector Current



Package Outline Dimensions

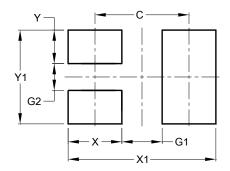
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
e	1	-	0.35		
L1	0.20	0.30	0.25		
L2	L2 0.20 0.30 0.25				
L3	-	-	0.40		
z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.70		
G1	0.30		
G2	0.20		
X	0.40		
X1	1.10		
Y	0.25		
Y1	0.70		



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